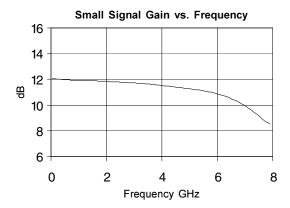


Product Description

Stanford Microdevices' NGA-689 is a high performance Gallium Arsenide Heterojunction Bipolar Transistor MMIC Amplifier. Designed with InGaP process technology for improved reliability, a Darlington configuration is utilized for broadband performance up to 5 Ghz. The heterojunction increases breakdown voltage and minimizes leakage current between junctions. Cancellation of emitter junction non-linearities results in higher suppression of intermodulation products.



NGA-689

DC-5000 MHz, Cascadable GaAs HBT MMIC Amplifier



Product Features

- 11.7dB Gain, 18.9 dBm P1dB at 1950Mhz
- Cascadable 50 ohm: 1.4:1 VSWR
- Patented GaAs HBT Technology
- Operates from Single Supply
- Low Thermal Resistance Package
- Unconditionally Stable

Applications

- Cellular, PCS, CDPD
- Wireless Data, SONET

Symbol	Parameters: Test Conditions: Z ₀ = 50 Ohms, I _D = 80 mA, T = 25°C		Units	Min.	Тур.	Max.
P _{1dB}	Output Power at 1dB Compression	f = 850 MHz f = 1950 MHz f = 2400 MHz	dBm dBm dBm		19.9 18.9 17.9	
IP ₃	Third Order Intercept Point Power out per tone = 0 dBm	f = 850 MHz f = 1950 MHz f = 2400 MHz	dBm dBm dBm		36.9 33.6 32.1	
S ₂₁	Small Signal Gain	f = 850 MHz f = 1950 MHz f = 2400 MHz	dB dB dB		11.9 11.7 11.6	
Bandwidth	Determined by S11 and S22 values		MHz		5000	
S ₁₁	Input VSWR	f = DC - 5000 MHz	=		1.4:1	
S ₂₂	Output VSWR	f = DC - 5000 MHz	=		1.4:1	
S ₁₂	Reverse Isolation	f = 850 MHz f = 1950 MHz f = 2400 MHz	dB dB dB		19.7 19.5 19.4	
NF	Noise Figure	f = 2000 MHz	dB		6.0	
V _D	Device Voltage		٧		5.8	
R _{th} , j-l	Thermal Resistance (junction - lead)	°C/W		91		

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Phone: (800) SMI-MMIC



Absolute Maximum Ratings

Operation of this device above any one of these parameters may cause permanent damage.

Bias Conditions should also satisfy the following expression: I_DV_D (max) < $(T_J - T_{OP})/R_{th}$, j-I

Parameter	Value	Unit
Supply Current	120	mA
Device Voltage	6.7	٧
Operating Temperature	-40 to +85	°C
Maximum Input Power	+13	dBm
Storage Temperature Range	-40 to +150	°C
Operating Junction Temperature	+150	°C

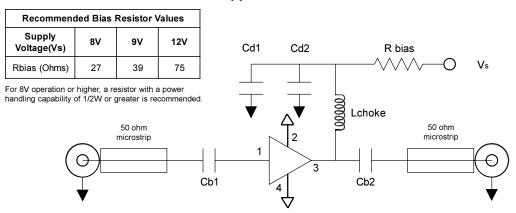
Key parameters, at typical operating frequencies:

noy parameters, at typical operating noqueneres.							
	Typical		Test Condition				
Parameter	25°C	Unit	(I _D = 80mA, unless otherwise noted)				
500 MHz							
Gain	12.0	dB					
Output IP3	37.2	dBm	Tone spacing = 1 MHz, Pout per tone = 0dBm				
Output P1dB	19.9	dBm					
Input Return Loss	19.6	dB					
Reverse Isolation	19.7	dB					
850 MHz							
Gain	11.9	dB					
Output IP3	36.9	dBm	Tone spacing = 1 MHz, Pout per tone = 0dBm				
Output P1dB	19.9	dBm					
Input Return Loss	18.5	dB					
Reverse Isolation	19.7	dB					
1950 MHz							
Gain	11.7	dB					
Output IP3	33.6	dBm	Tone spacing = 1 MHz, Pout per tone = 0dBm				
Output P1dB	18.9	dBm					
Input Return Loss	16.0	dB					
Reverse Isolation	19.5	dB					
2400 MHz							
Gain	11.6	dB					
Output IP3	32.1	dBm	Tone spacing = 1 MHz, Pout per tone = 0dBm				
Output P1dB	17.9	dBm					
Input Return Loss	15.9	dB					
Reverse Isolation	19.4	dB					



Pin #	Function	Description	Device Schematic
1	RF IN	RF input pin. This pin requires the use of an external DC blocking capacitor chosen for the frequency of operation.	
2	GND	Connection to ground. For best performance use via holes (as close to ground leads as possible) to reduce lead inductance.	
3	RF OUT/ BIAS	RF output and bias pin. Bias should be supplied to this pin through an external series resistor and RF choke inductor. Because DC biasing is present on this pin, a DC blocking capacitor should be used in most applications (see application schematic). The supply side of the bias network should be well bypassed.	
4	GND	Same as Pin 2.	

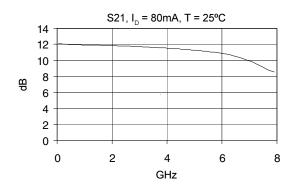
Application Schematic

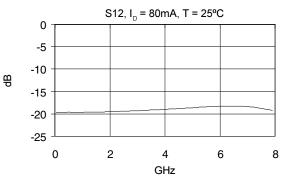


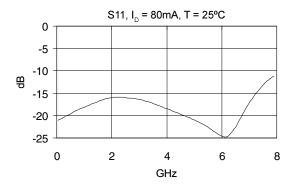
Reference Designator	Function	500 MHz	850 MHz	1950 M Hz	2400 MHz
Cb1	DC Blocking	220 pF	100 pF	68 pF	56 pF
Cb2	DC Blocking	220 pF	100 pF	68 pF	56 pF
Cd1	Decoupling	1 uF	1 uF	1 uF	1 uF
Cd2	Decoupling	100 pF	68 pF	22 pF	22 pF
Lchoke	AC Blocking	68 nH	33 nH	22 nH	18 nH

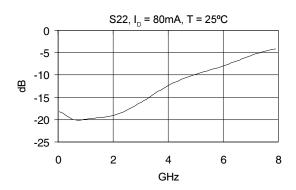


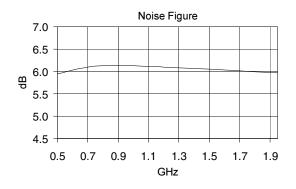


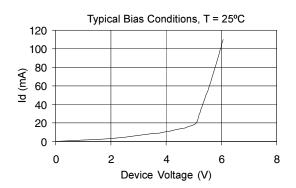






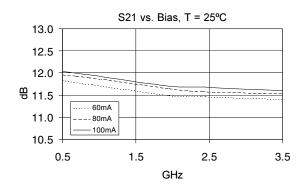


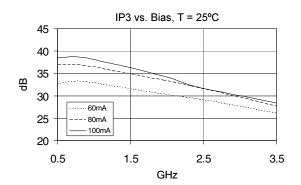


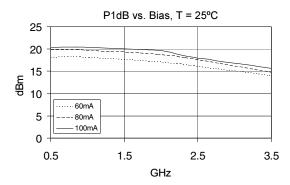


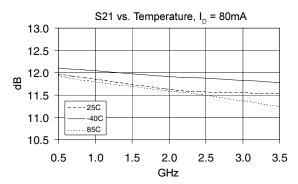


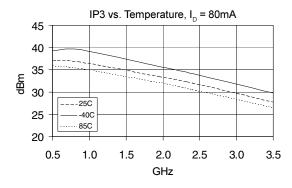


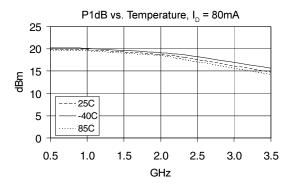
















Typical S-Parameters, I_D = 80mA (No external matching, de-embedded to device leads)

	S.	11		S21			S12		s	22
Freq GHz	mag	Ang	dB	mag	Ang	dB	mag	Ang	mag	Ang
0.05	0.089	2	12.1	4.014	175	-19.7	0.103	0	0.124	-180
0.10	0.090	1	12.1	4.009	174	-19.7	0.103	0	0.121	-179
0.20	0.093	-1	12.0	3.997	173	-19.7	0.104	-2	0.116	-178
0.30	0.097	-4	12.0	3.985	170	-19.7	0.104	-3	0.111	-177
0.40	0.101	-7	12.0	3.976	168	-19.7	0.104	-4	0.106	-175
0.50	0.105	-10	12.0	3.968	165	-19.7	0.104	-6	0.101	-173
0.60	0.109	-12	12.0	3.964	162	-19.7	0.104	-7	0.099	-171
0.70	0.114	-14	12.0	3.959	159	-19.7	0.104	-8	0.098	-168
0.80	0.117	-16	11.9	3.955	156	-19.7	0.104	-9	0.099	-167
0.90	0.120	-18	11.9	3.950	153	-19.7	0.104	-10	0.100	-165
1.00	0.124	-20	11.9	3.948	150	-19.7	0.104	-11	0.100	-164
1.10	0.128	-22	11.9	3.944	147	-19.7	0.104	-12	0.102	-163
1.20	0.131	-24	11.9	3.940	144	-19.7	0.104	-13	0.103	-162
1.30	0.135	-26	11.9	3.936	141	-19.6	0.104	-14	0.104	-161
1.40	0.140	-28	11.9	3.931	138	-19.6	0.104	-16	0.105	-161
1.50	0.144	-29	11.9	3.928	135	-19.6	0.104	-17	0.106	-161
1.60	0.148	-31	11.9	3.923	132	-19.6	0.105	-18	0.106	-161
1.70	0.152	-32	11.9	3.920	129	-19.6	0.105	-19	0.107	-161
1.80	0.156	-34	11.9	3.916	126	-19.6	0.105	-20	0.108	-162
1.90	0.158	-36	11.8	3.911	123	-19.5	0.105	-21	0.110	-164
2.00	0.159	-38	11.8	3.907	120	-19.5	0.106	-22	0.111	-166
2.20	0.161	-43	11.8	3.898	113	-19.5	0.106	-25	0.116	-172
2.40	0.160	-47	11.8	3.889	107	-19.4	0.107	-27	0.123	-179
2.60	0.158	-53	11.8	3.878	101	-19.4	0.107	-30	0.133	174
2.80	0.155	-57	11.7	3.866	95	-19.3	0.108	-32	0.143	167
3.00	0.151	-60	11.7	3.854	89	-19.3	0.109	-35	0.156	160
3.20	0.146	-63	11.7	3.838	83	-19.2	0.109	-37	0.170	154
3.40	0.140	-66	11.6	3.823	76	-19.2	0.110	-40	0.186	147
3.60	0.133	-69	11.6	3.805	70	-19.1	0.111	-43	0.204	142
3.80	0.126	-71	11.6	3.785	64	-19.0	0.112	-45	0.222	136
4.00	0.120	-74	11.5	3.766	58	-19.0	0.112	-48	0.240	131
4.20	0.113	-76	11.5	3.745	51	-18.9	0.113	-51	0.258	126
4.40	0.107	-78	11.4	3.723	45	-18.9	0.114	-54	0.276	121
4.60	0.101	-80	11.4	3.702	38	-18.8	0.115	-57	0.292	116
4.80	0.095	-82	11.3	3.679	32	-18.7	0.116	-60	0.308	111
5.00	0.089	-83	11.3	3.655	26	-18.6	0.117	-63	0.323	106
5.20	0.084	-84	11.2	3.630	19	-18.5	0.118	-67	0.337	101
5.40	0.078	-84	11.1	3.602	13	-18.5	0.119	-70	0.351	95
5.60	0.071	-81 -75	11.1	3.574	6	-18.4	0.120	-74	0.365	89
5.80 6.00	0.064	-75 65	11.0 10.9	3.538	-1	-18.3 -18.3	0.121	-77	0.382	82
	0.059	-65		3.496 3.349	-7		0.122	-81 -91	0.399 0.455	76
6.50 7.00		-26	10.5		-25	-18.3	0.122			58
7.50	0.138 0.220	-11 -11	9.9	3.138 2.863	-42 -59	-18.4 -18.8	0.120 0.115	-102 -112	0.521 0.583	41 25
7.50	0.220	-11 -15	8.5	2.863	-59 -70	-18.8 -19.1		-112	0.583	16
7.90	0.276	-15	0.5	2.072	-/0	-19.1	0.110	-119	0.021	ıθ





Caution: ESD sensitive Appropriate precautions in handling, packaging and testing devices must be observed.

NGA-689 DC-5.0 GHz 5.8V GaAs HBT

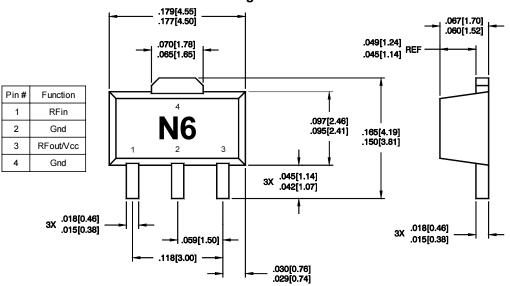
Part Number Ordering Information

Part Number	Reel Size	Devices/Reel	
NGA-689	7"	1000	

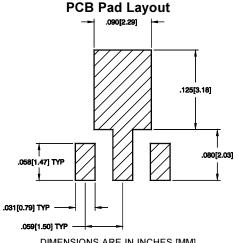
Part Symbolization

The part will be symbolized with a "N6" designator on the top surface of the package.

Package Dimensions



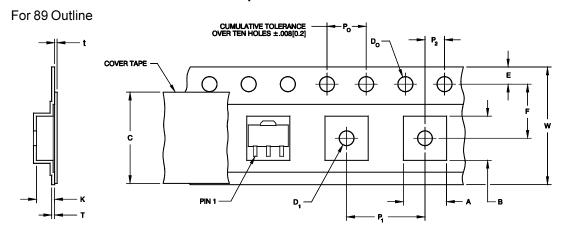
Pin assignments shown for reference only, not marked on part





Component Tape and Reel Packaging

Tape Dimensions



DETAIL A

		Size			
	Description	Symbol	Millimeters	Inches	
Cavity	Length Width Depth	A B K	4.91 +/- 0.01 4.52 +/- 0.01 1.90 +/- 0.01	0.19 +/- 0.0004 0.18 +/- 0.0004 0.07 +/- 0.0004	
	Pitch Bottom Hole Diameter	P ₁ D ₁	8.00 +/- 0.01 1.60 +/- 0.10	0.07 +/- 0.0004 0.31 +/- 0.0004 0.06 +/- 0.004	
Perforation	Diameter Pitch Position	D _o P _o E	1.55 +/- 0.05 4.00 +/- 0.01 1.75 +/- 0.01	0.06 +/- 0.002 0.16 +/- 0.0004 0.07 +/- 0.0004	
Cover Tape	Width Tape Thickness	C t	9.10 +/- 0.25 0.05 +/- 0.01	0.36 +/- 0.01 0.002 +/- 0.0004	
Carrier Tape	Width Thickness	W T	12.0 +/- 0.03 0.30 +/- 0.05	0.47 +/- 0.001 0.01 +/- 0.002	
Distance	Cavity to Perforation (Width Direction) Cavity to Perforation (Length Direction)	F P ₂	5.50 +/- 0.10 2.00 +/- 0.10	0.22 +/- 0.0004 0.08 +/- 0.0004	

Note: Drawing not to scale